REVELUTION The Impact of Emerging Memory





Thursday, August 23, 12















NVM Bitcell





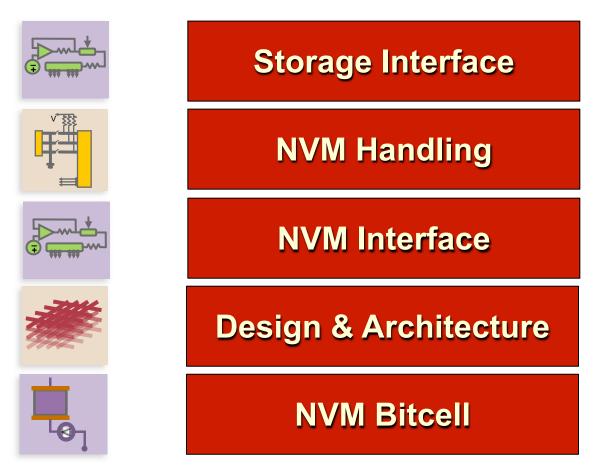




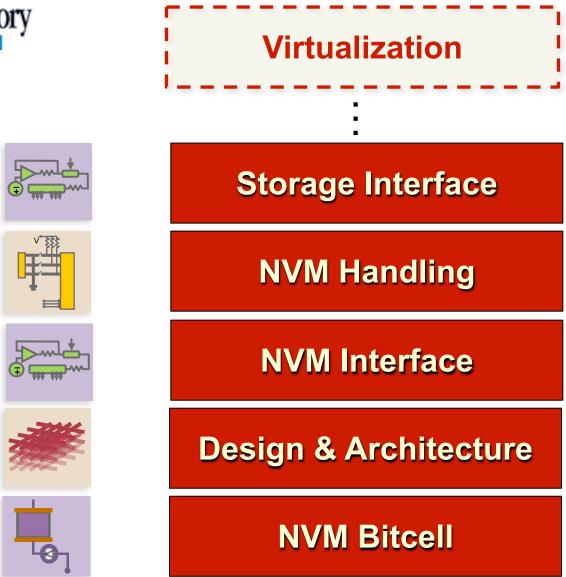




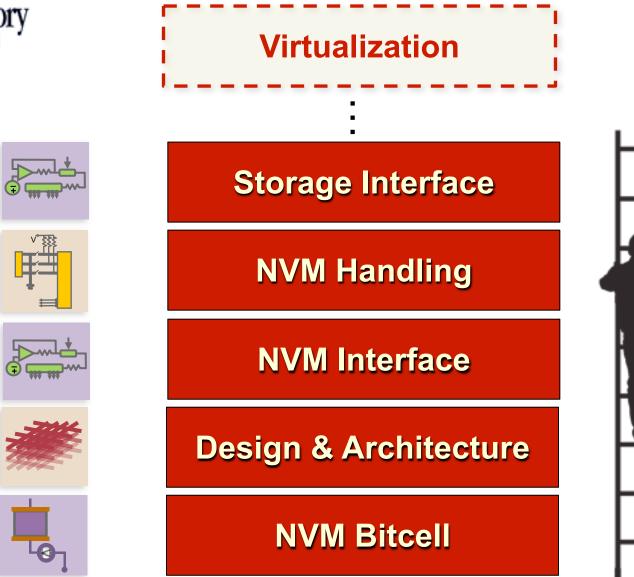














Storage Interface

NVM Handling

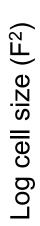
NVM Interface

Design & Architecture



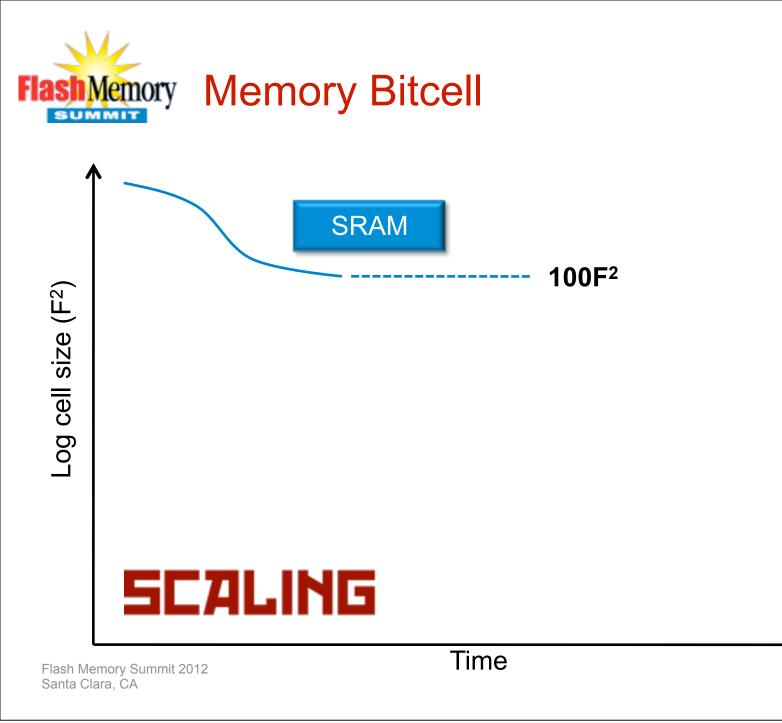
NVM Bitcell

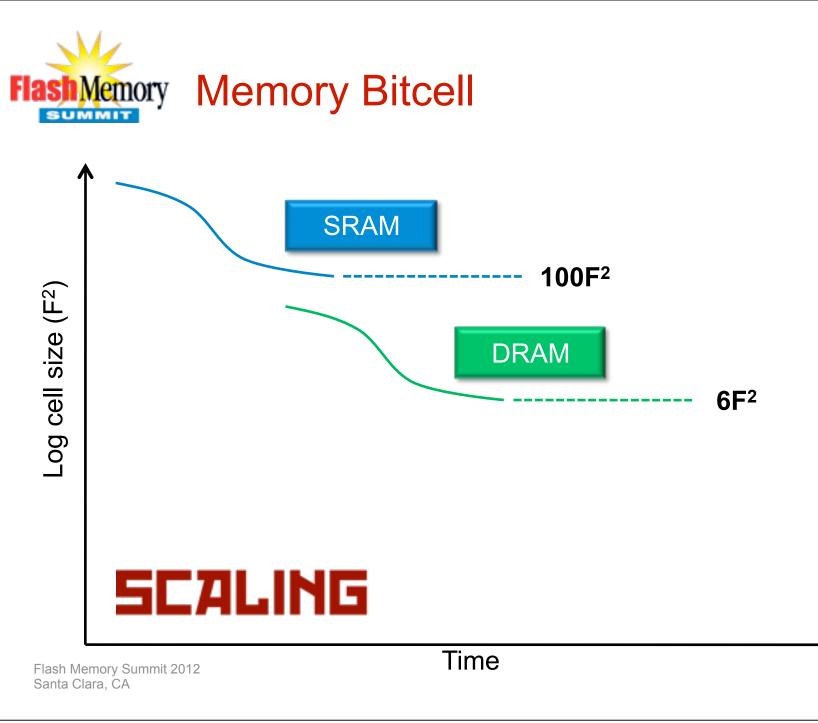


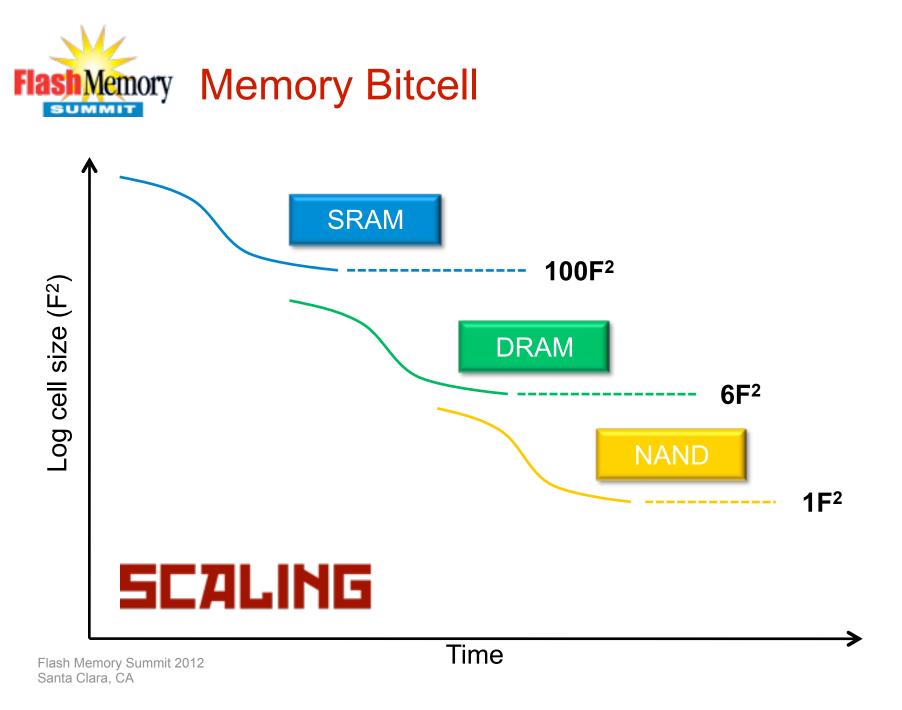


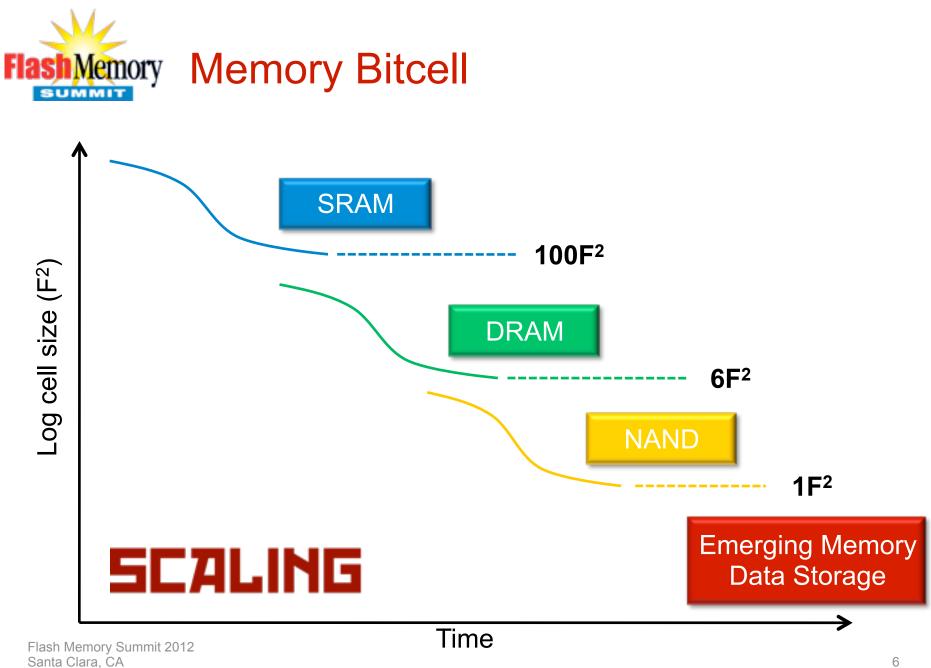


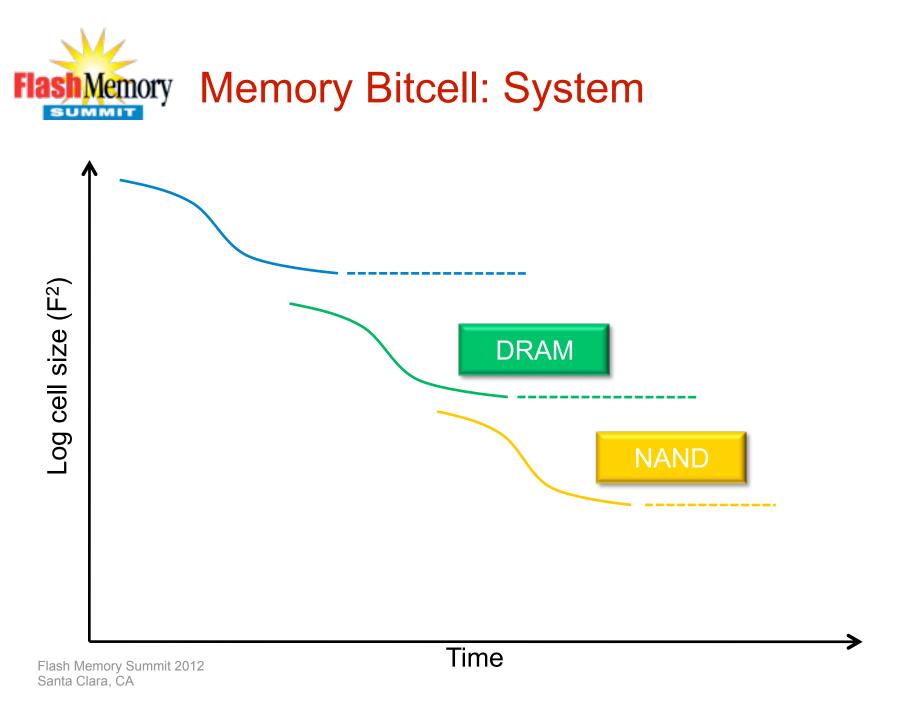
Time

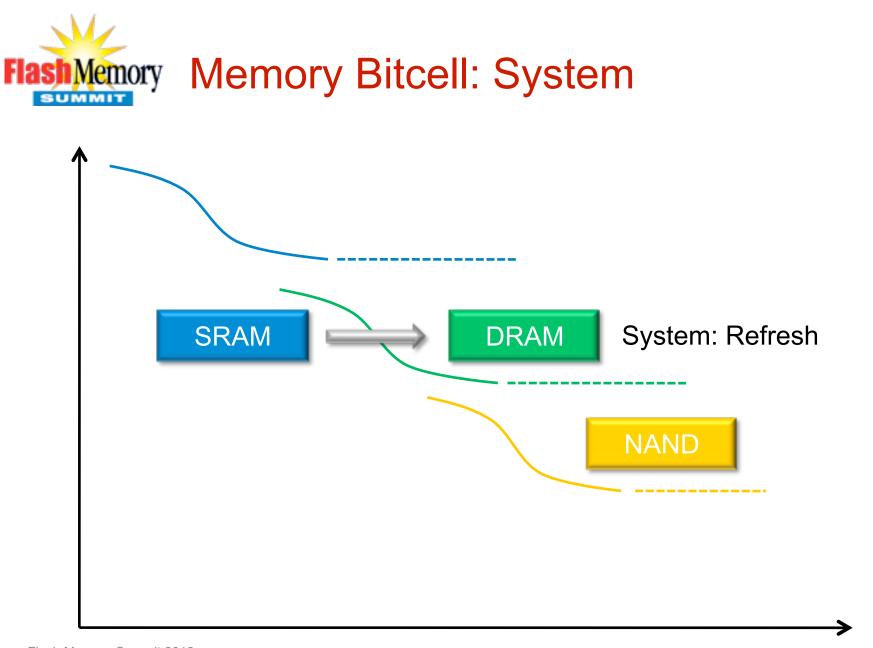


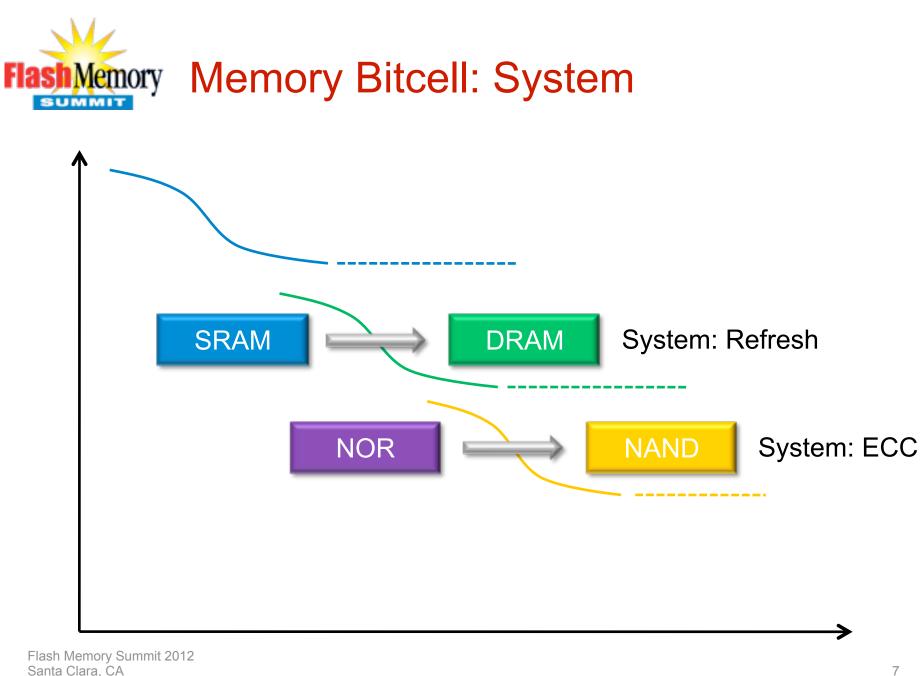










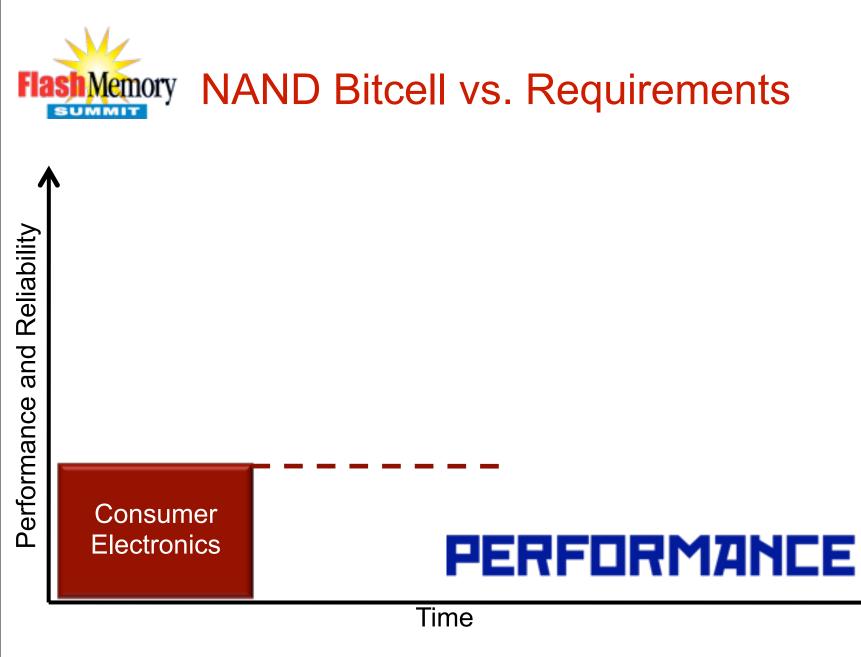


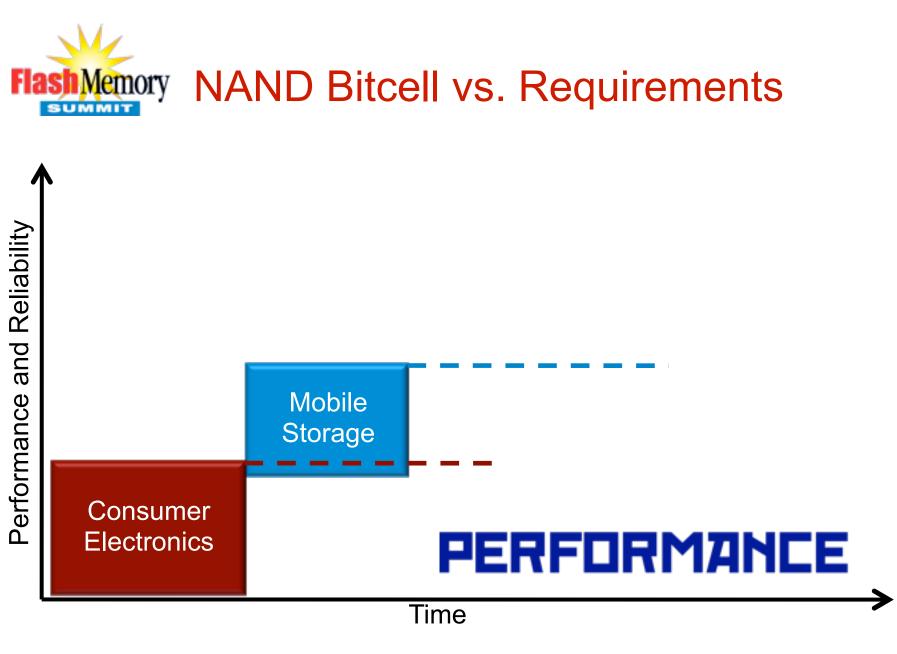


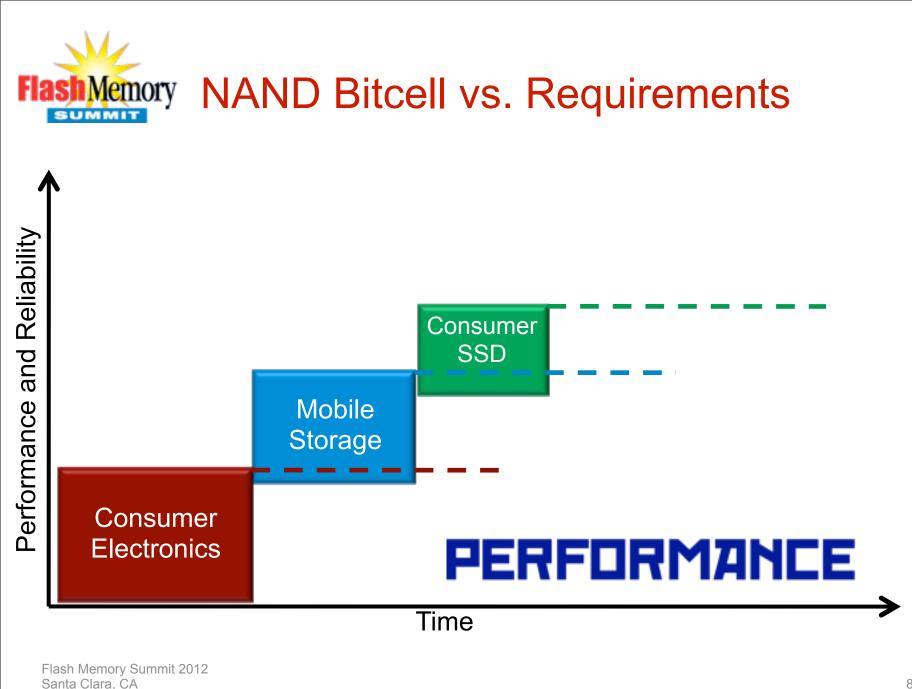
PERFORMANCE

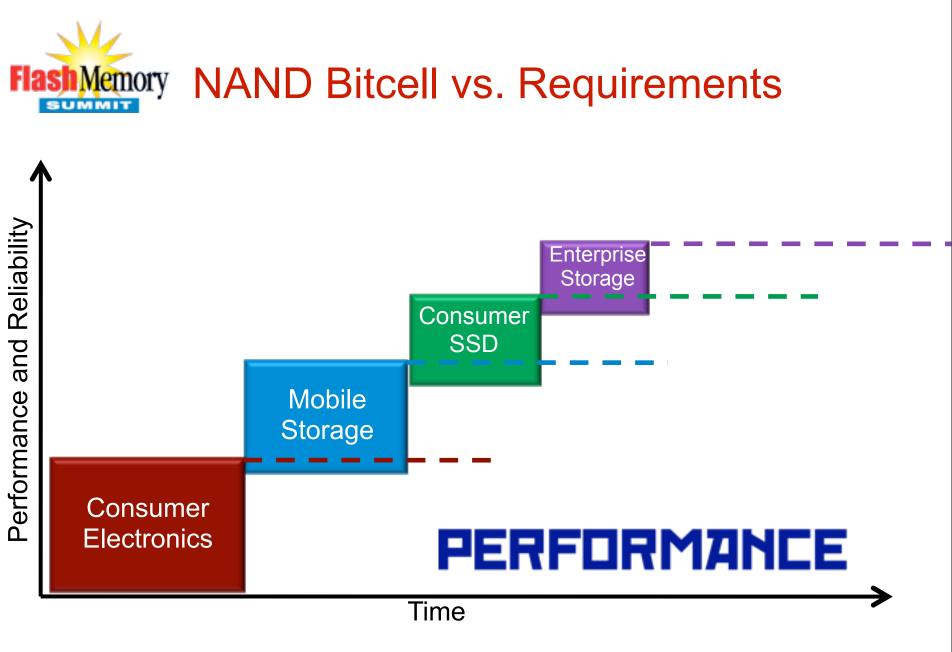
Time

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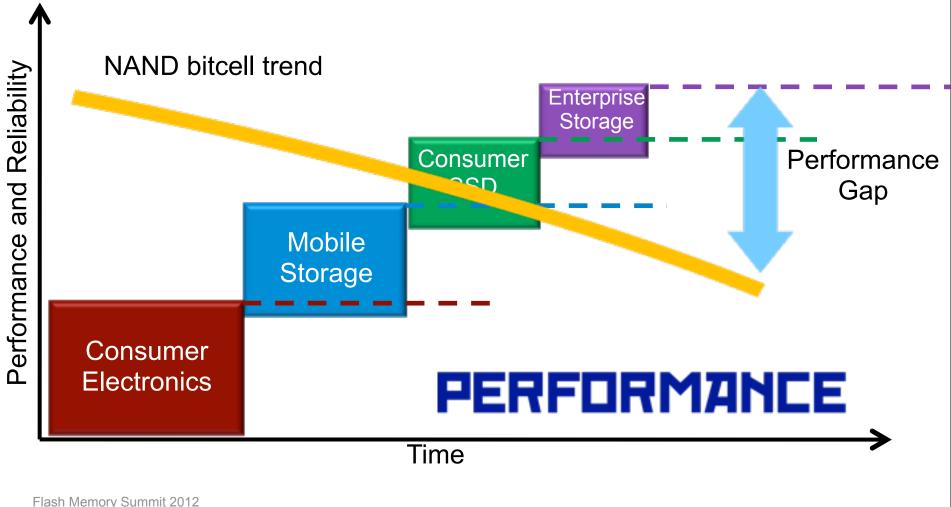








Flash Memory NAND Bitcell vs. Requirements

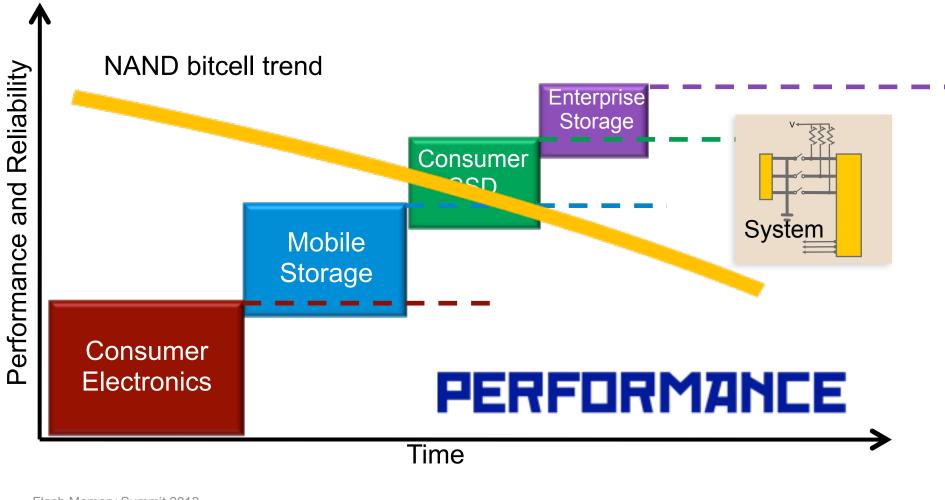


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Santa Clara, CA



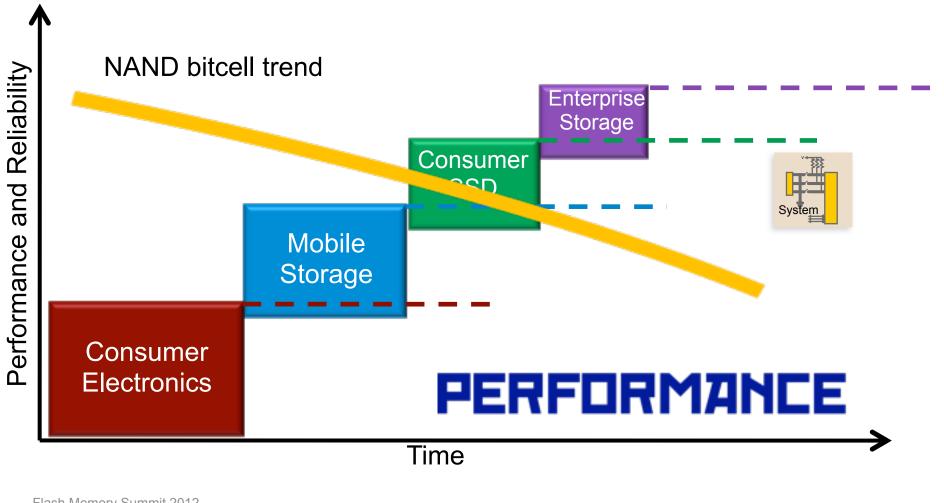
Flash Memory NAND Bitcell vs. Requirements



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Flash Memory NAND Bitcell vs. Requirements



8



Flash Memory Key Criteria for Emerging Memory



Flash Memory Key Criteria for Emerging Memory

SCALING

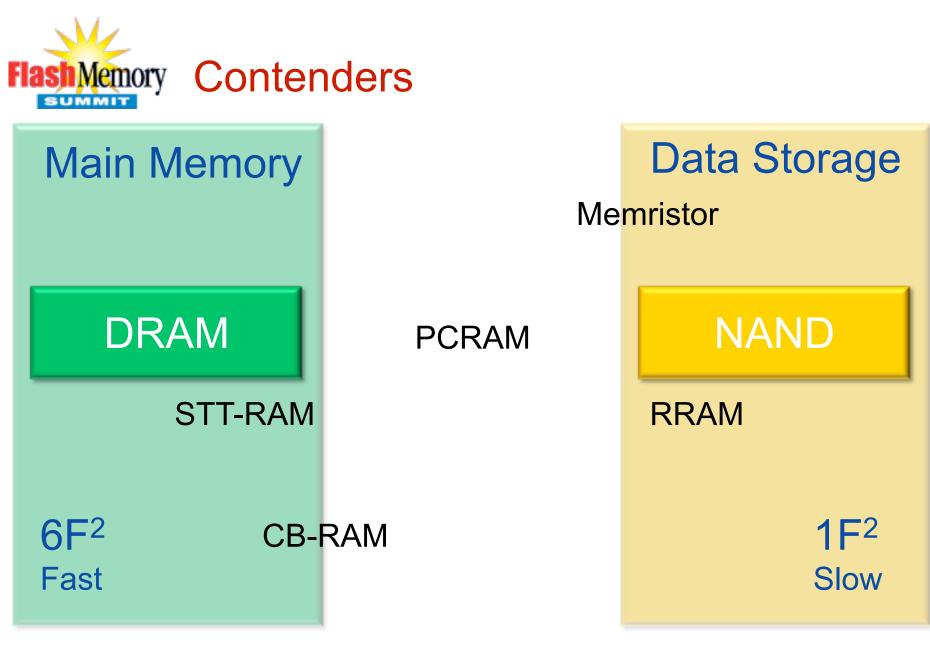
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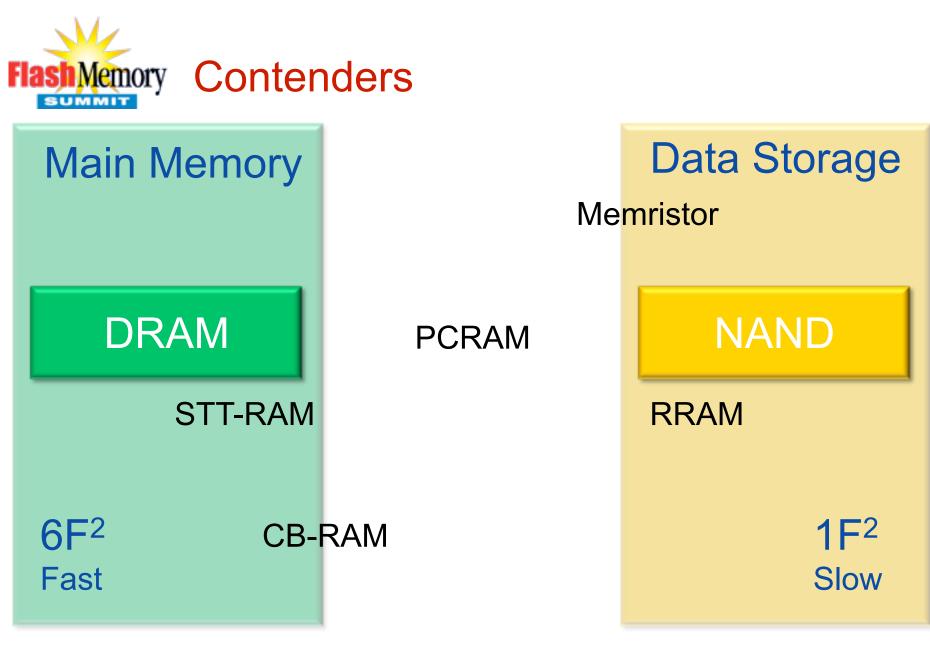


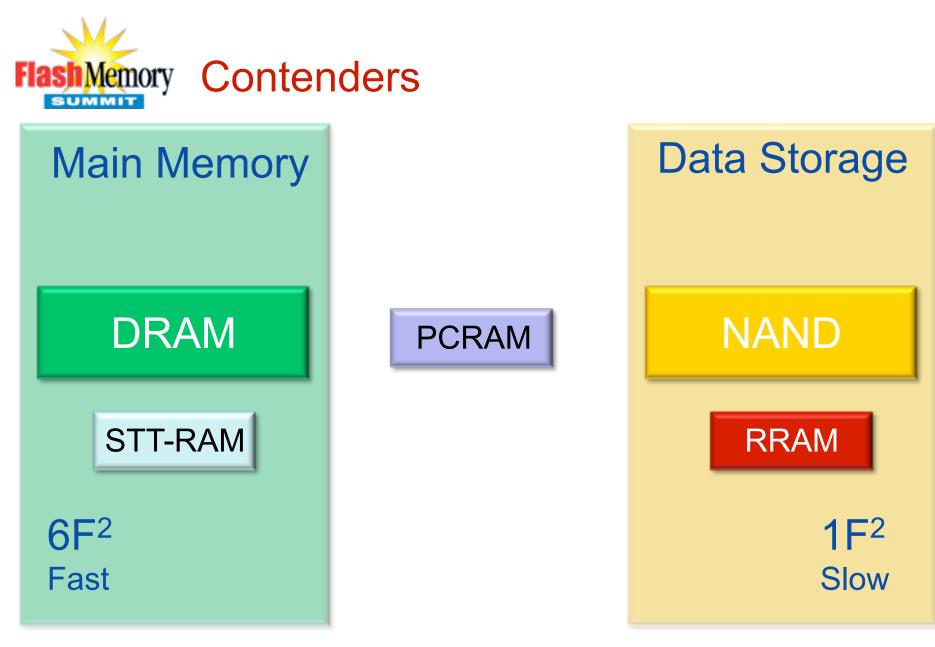
Memory Key Criteria for Emerging Memory

SCALING

PERFORMANCE









	STT-RAM	PCRAM	RRAM	NAND
Memory Cell (F ²)	$30F^2 \rightarrow 6F^2$	$10F^2 \rightarrow 5F^2$	$20F^2 \rightarrow 0.25F^2$	$4.5F^2 \rightarrow 1F^2$
Cell type	1T-1R	1T-1R 1D-1R	1T-1R 1D-1R 1R	1T-FG
Write Speed (Bit level)	1's ns	10's ns	10's ns ~ 100's ns	10,000 ns
Application	Embedded Main memory	Code storage NV cache	Data storage NV cache Embedded	Data storage

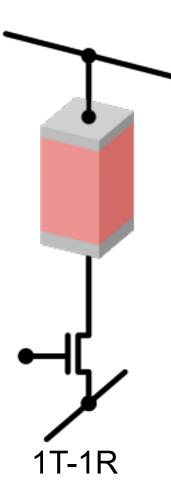


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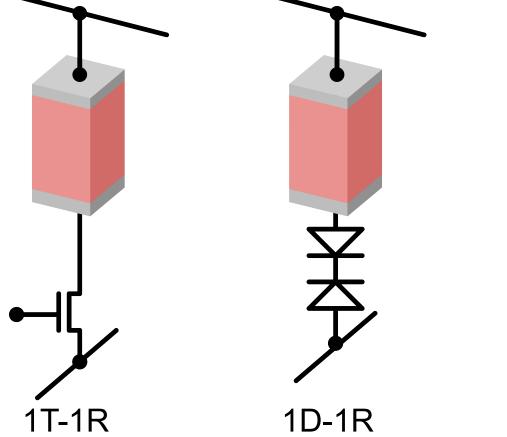




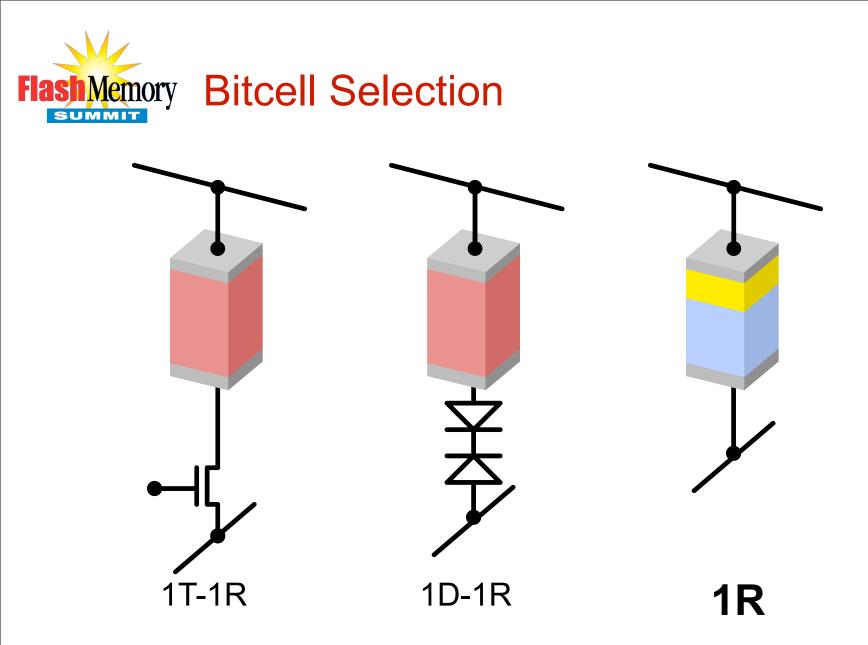
1D-1R





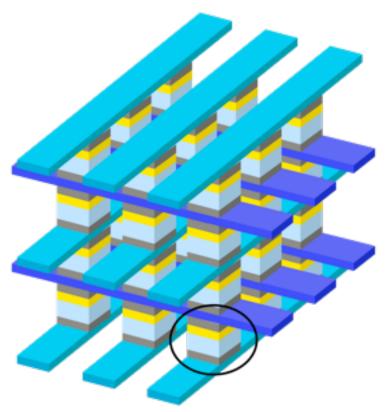


1R





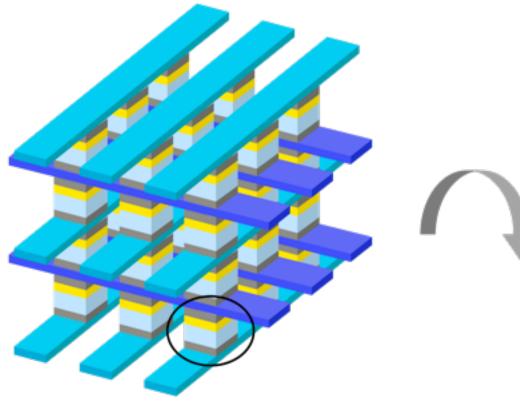
Stacked Planar



4F²/N 2 Masks per Layer



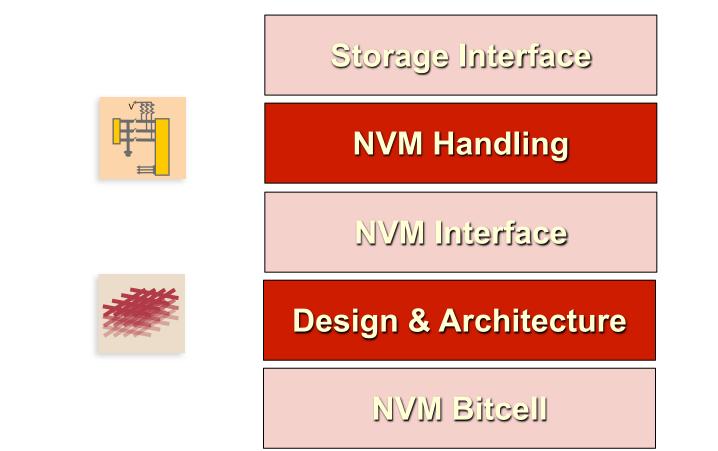
Stacked Vertical



4F²/N 2 Masks per Layer

2F²/N 2 Masks per 8 Layers







Flash Memory NVM Handling: \$1B+

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Memory NVM Handling: \$1B+







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Memory NVM Handling: \$1B+







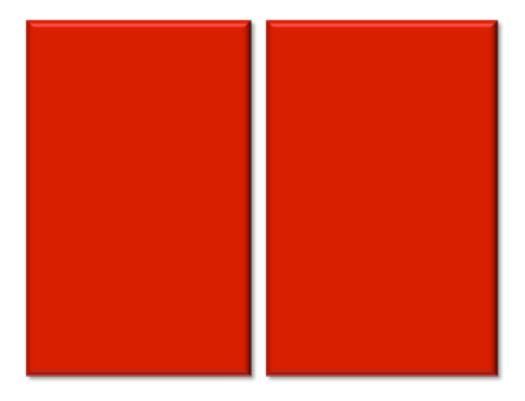
NVM handling makes failing NAND bitcells usable
Requires deep knowledge of bitcell & architecture

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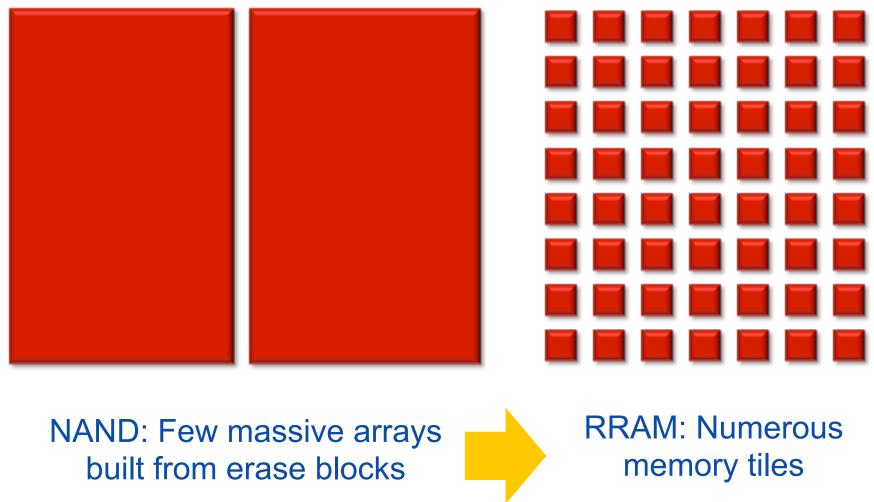




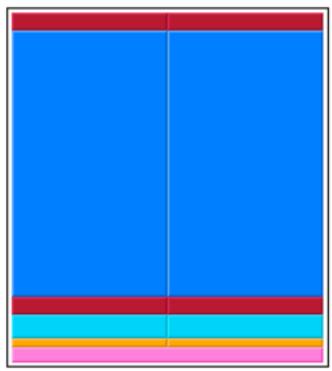


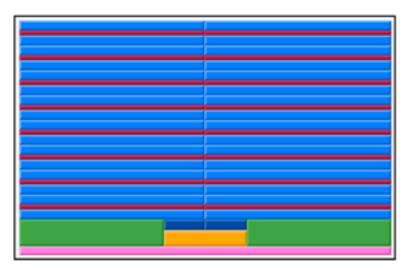
NAND: Few massive arrays built from erase blocks







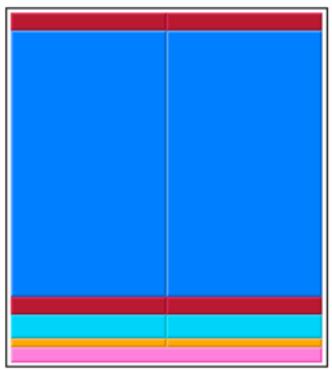


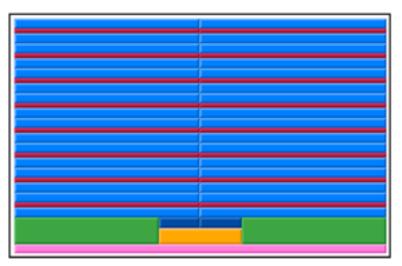


1Tb 1R 3D-RRAM (projected)

256Gb PBiCS 3D-NAND (projected)

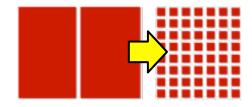






1Tb 1R 3D-RRAM (projected)

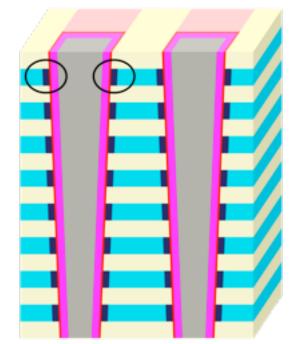
256Gb PBiCS 3D-NAND (projected)





Flash Memory NVM Handling: Examples

Stacked Vertical



$\begin{array}{c} {}^{2F^2/N}\\ {}^{2\,Masks\,per\,8\,Layers}\\ 2D \rightarrow 3D \ Bit\\ Interference\end{array}$

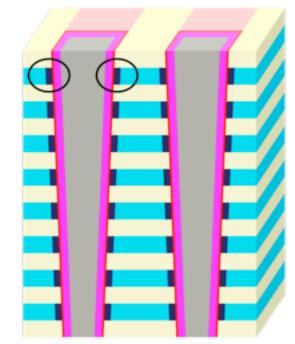
Block \rightarrow Tile Management



Flash Memory NVM Handling: Examples

Stacked Vertical

PAGES!



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Flash Memory NVM Handling: Examples

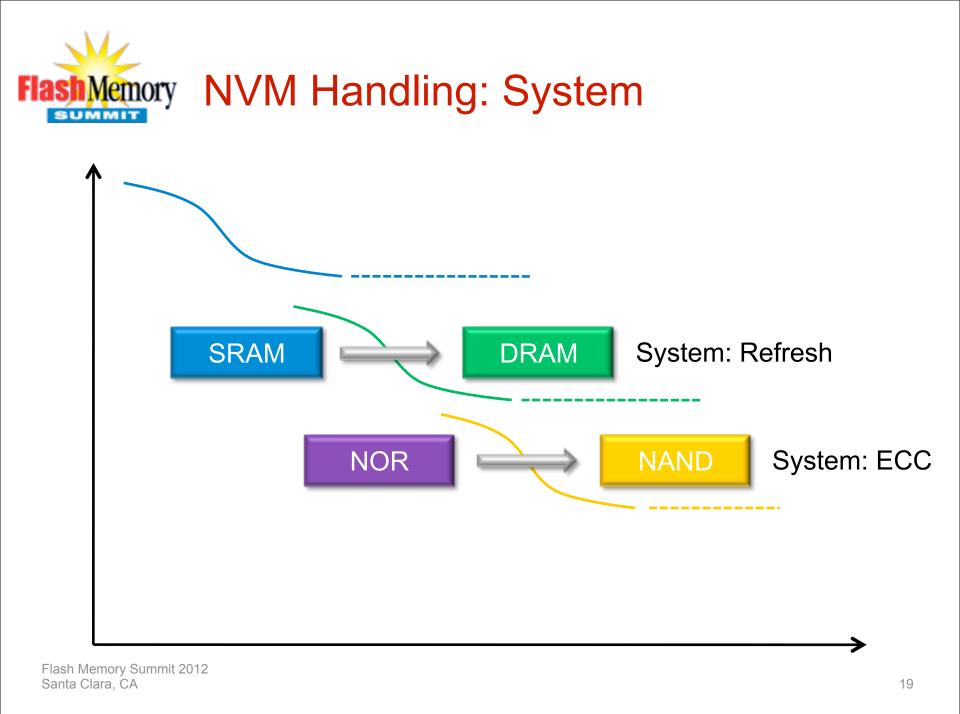
Stacked Vertical

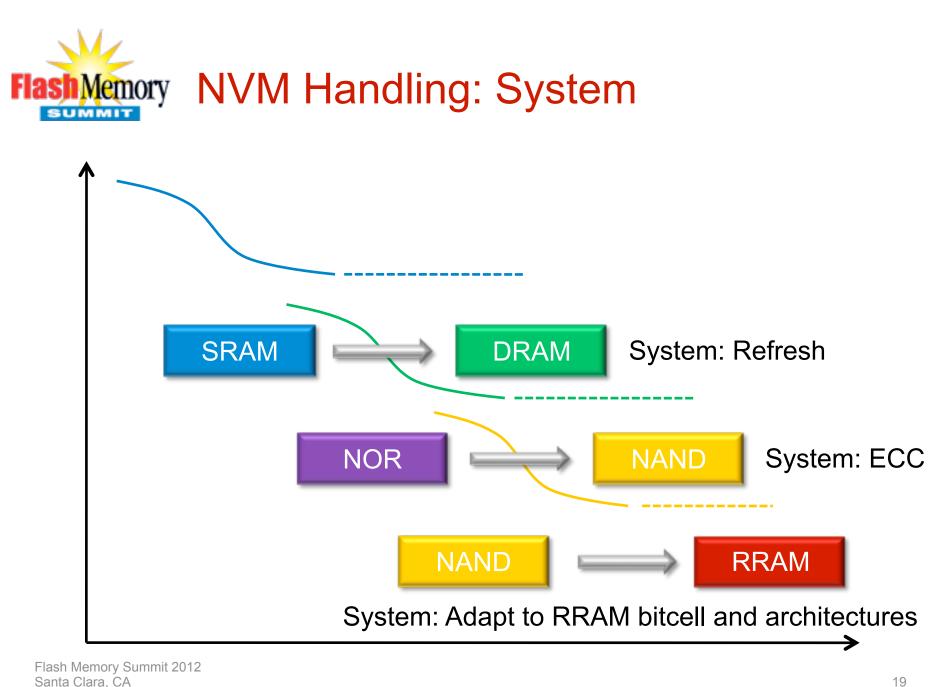




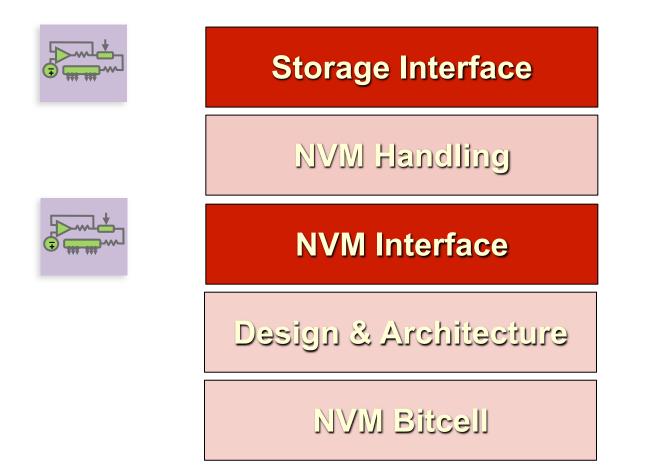
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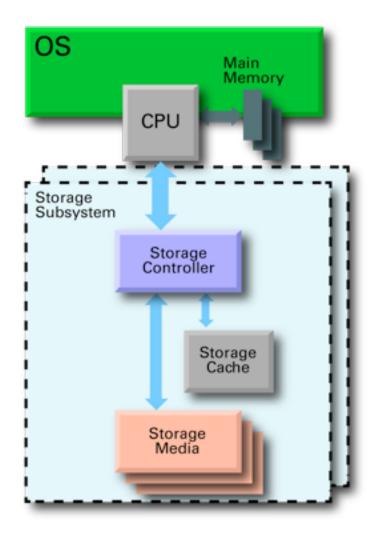






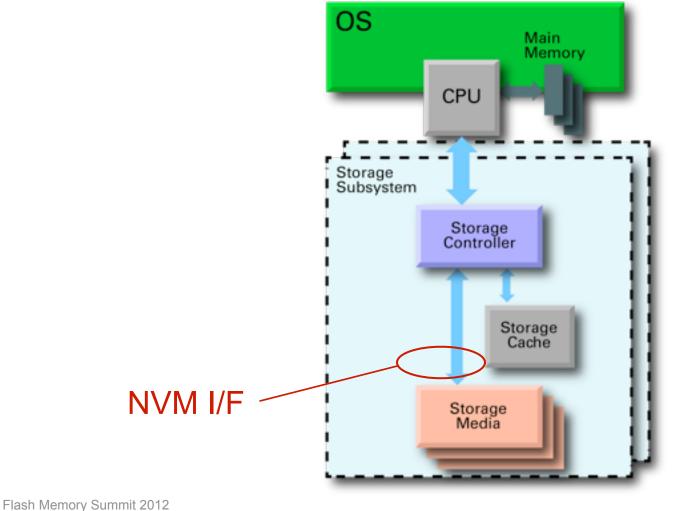


Flash Memory Interfaces in a Storage System





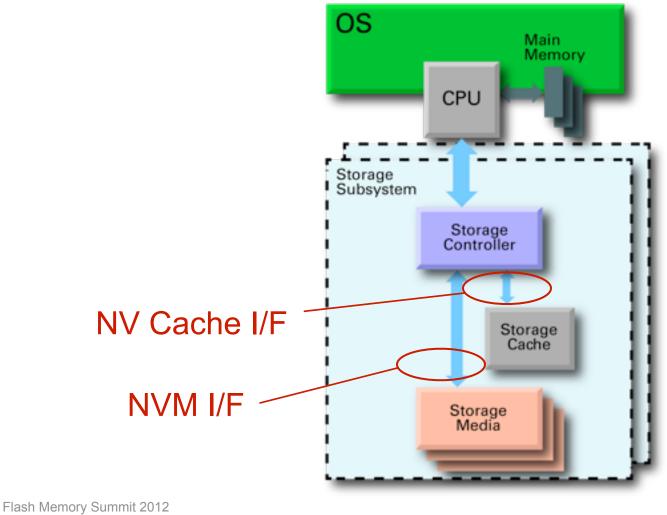
Flash Memory Interfaces in a Storage System



Santa Clara, CA



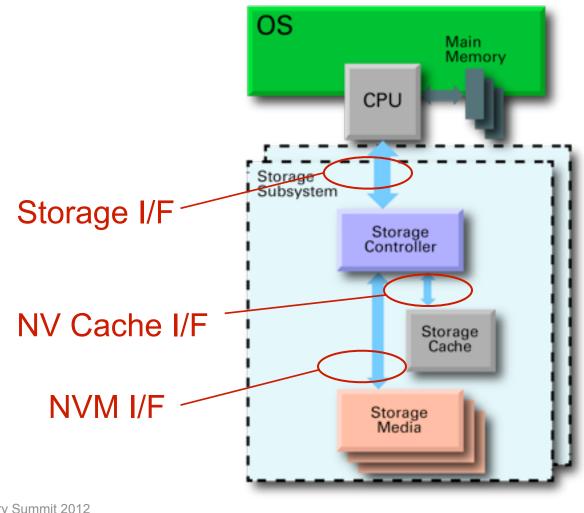
FlashMemory Interfaces in a Storage System



Santa Clara, CA

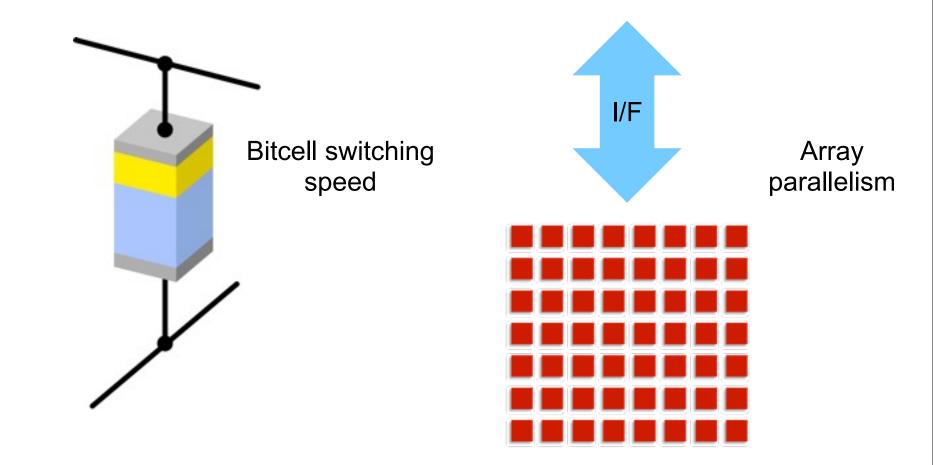


Flash Memory Interfaces in a Storage System

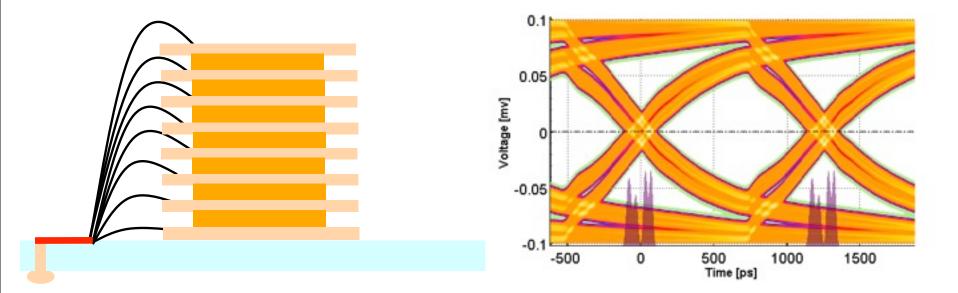




Flash Memory Driving the NVM Interface speed



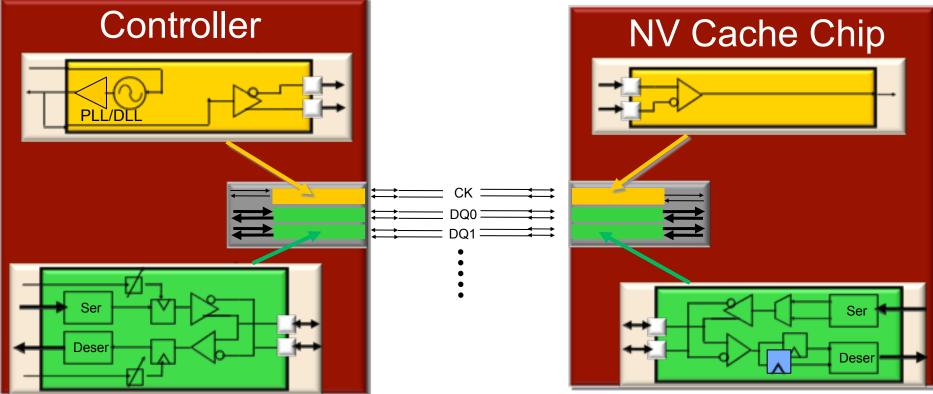




Capacity	8 loads	16 loads
Max Data Rate per pin	1.2+Gbps	1Gbps

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Total Signal Pins (DQ)	Max Data Rate per pin	Read Latency
10 (4 DQ)	4Gbps	Low, Deterministic



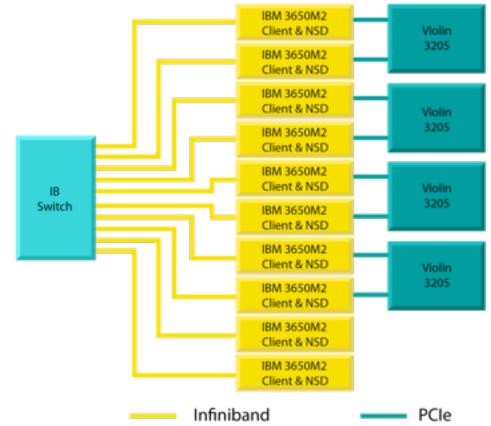
Storage: Real World Example

Project Presto! (2011)

IBM research demonstrated the ability to do policy guided storage management for 10 Billion file environment in 43 minutes. Previous record was 1,591 minutes

- Used cluster of 10 IBM xSeries servers
- IBM's cluster file system (GPFS)
- Placing file system's metadata on new solid-state storage appliance from Violin Memory

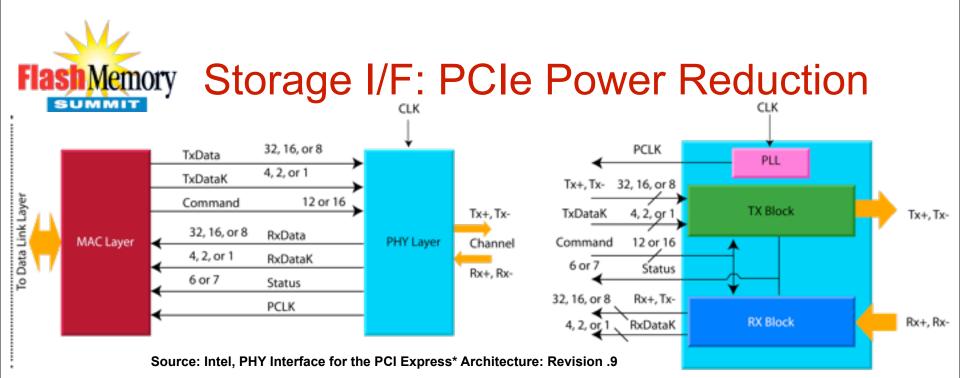




Cooling is the number one concern.

- Server and storage failure due to sustaining high resource utilization.

Flash Memory Summit 2012 Santa Clara, CA Source: Storage Class Memory: Technologies, Systems and Applications – FAST, February 2012



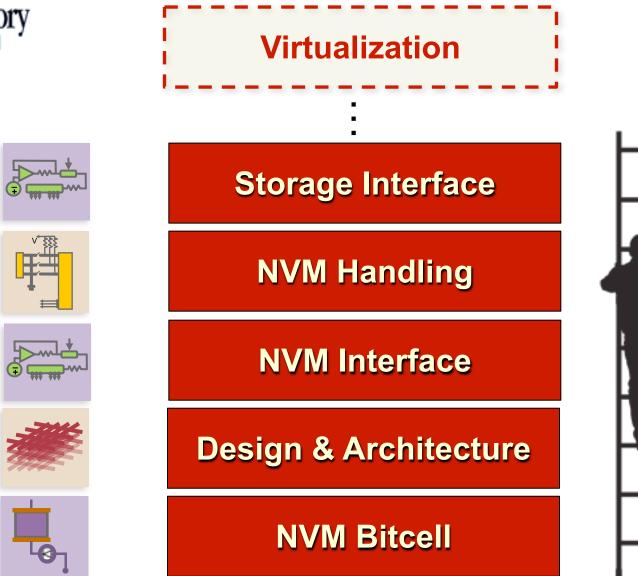
Active Power Optimization

- L1 sub-states => finer granularity power management
- Dynamic Bus Sizing Scaling bus width based on changing bandwidth needs
- Resonant techniques to recirculate clock energy

Idle Power Optimization

- Fast power On/Off circuits => Deeper power down
- Leakage control
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INTELLIGENCE -----> MEMORY



INTELLIGENCE -----> MEMORY

BEOL MEMORY & LOGIC INTEGRATION

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INTELLIGENCE -----> MEMORY

BEOL MEMORY & LOGIC INTEGRATION

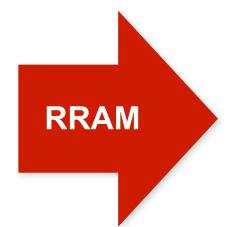
MESH COMPUTING WITH RRAM STORAGE NODES

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Thursday, August 23, 12



2012	2014	2016	2018	2020+	





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RRAM	Phase 1: "High Value" Adoption •1T-1R RRAM •Embedded me •NV cache •New character high value •Not as cost se •Establish tech	emory ristics bring ensitive			



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- Bob Dylan





- Bob Dylan

"Some people feel the rain. Others just get wet."





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Visit us at Flash Memory Summit Booth #813

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REVELUTION The Impact of Emerging Memory



Each major transition in memory technology has been coupled with a revolution in system architectures that exploit the key advantages of the new memory. NAND flash enters its third decade of mass production as strong as ever, but it appears increasingly likely that a new non-volatile memory technology will emerge over the course of this decade to answer the demands of the data center and the mobile consumer.

What are the key advantages of these emerging memories?
What attributes are required to become the successor to NAND flash?

•What sort of revolution will these emerging memories bring to system architectures?

•How (and when) will these new memories bring change to the data center and mobile devices?

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